MOSFETs Silicon N-Channel MOS (π-MOSVIII)

TK3P80E

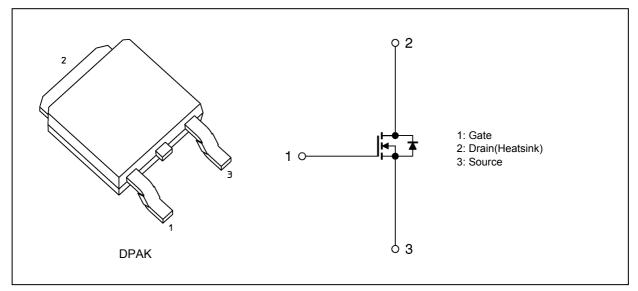
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 3.9 \Omega$ (typ.)
- (2) Low leakage current : $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 640 \ V)$
- (3) Enhancement mode: V_{th} = 2.5 to 4.0 V (V_{DS} = 10 V, I_D = 0.3 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \degree$ C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			V _{DSS}	800	V
Gate-source voltage			V _{GSS}	±30	7
Drain current (DC)		(Note 1)	Ι _D	3	A
Drain current (pulsed)		(Note 1)	I _{DP}	9	
Power dissipation	(T _c = 25°C)		PD	80	W
Single-pulse avalanche energy		(Note 2)	E _{AS}	118	mJ
Avalanche current			I _{AR}	3	Α
Reverse drain current (DC)		(Note 1)	I _{DR}	3	7
Reverse drain current (pulsed)		(Note 1)	I _{DRP}	9	7
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	1

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2014-02 2014-09-17

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance		1.56	°C/W

Note 1: Ensure that the channel temperature does not exceed 150 °C. Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 23.8 mH, R_G = 25 Ω , I_{AR} = 3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V_{DS} = 640 V, V_{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	800	_	_	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.3 mA	2.5	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 1.5 A	_	3.9	4.9	Ω

6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz	_	500	—	pF
Reverse transfer capacitance	C _{rss}		_	4	_	
Output capacitance	C _{oss}		_	40	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	5.0	_	Ω
Switching time (rise time)	tr	See Fig. 6.2.1.	_	25	_	ns
Switching time (turn-on time)	t _{on}		_	50	_	
Switching time (fall time)	t _f		_	22	_	
Switching time (turn-off time)	t _{off}		_	70	_	
MOSFET dv/dt ruggedness	dv/dt	$V_{DD} = 0$ to 400 V, $I_D = 3$ A	10		_	V/ns

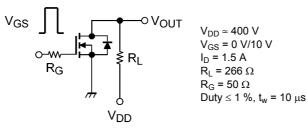


Fig. 6.2.1 Switching Time Test Circuit

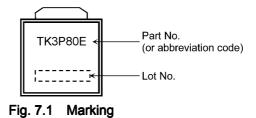
6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 3 A	_	12	—	nC
Gate-source charge 1	Q _{gs1}		_	4	_	
Gate-drain charge	Q _{gd}			5	_	

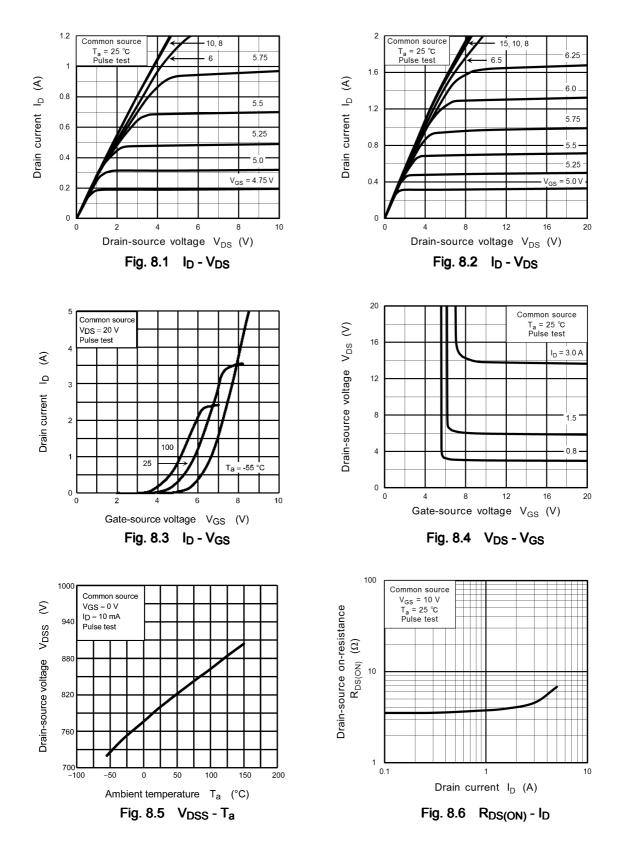
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

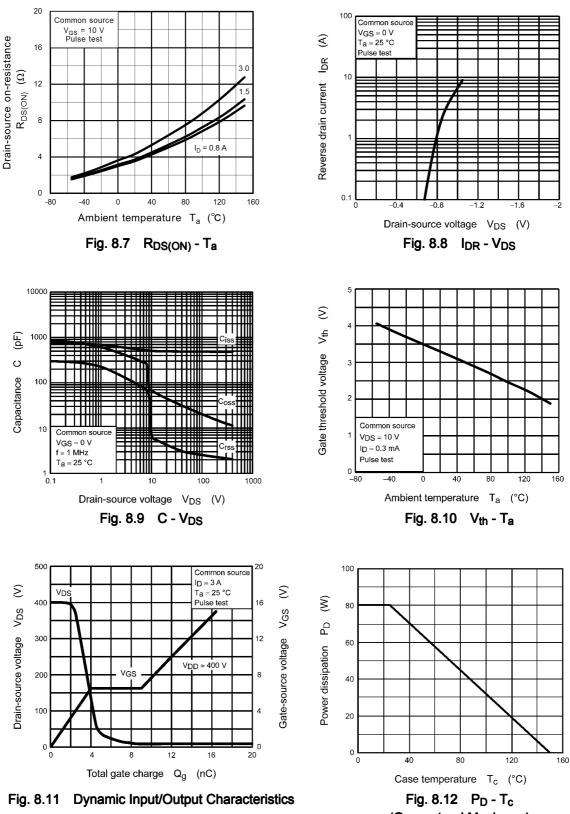
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 3 A, V _{GS} = 0 V	—	_	-1.7	V
Reverse recovery time		I _{DR} = 3 A, V _{GS} = 0 V	_	800	—	ns
Reverse recovery charge	Q _{rr}	_dI _{DR} /dt = 100 A/μs	_	3.5	_	μC
Peak reverse recovery current	I _{rr}			11	_	A

7. Marking

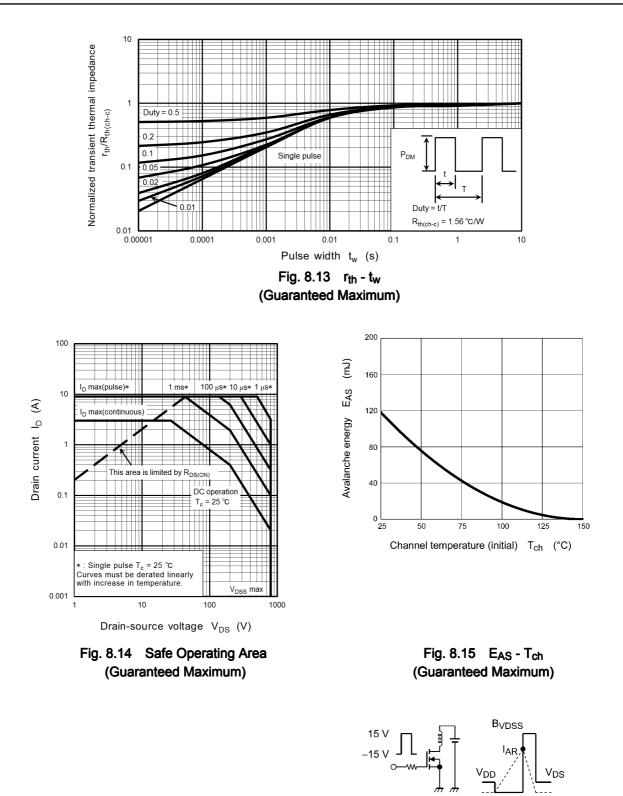


8. Characteristics Curves (Note)





(Guaranteed Maximum)



 $R_{G} = 25 \Omega, V_{DD} = 90 V E_{AS} = \frac{1}{2} \cdot L \cdot I^{2}_{AR} \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}}\right)$ Fig. 8.16 Test Circuit/Waveform

Waveform

Test Circuit

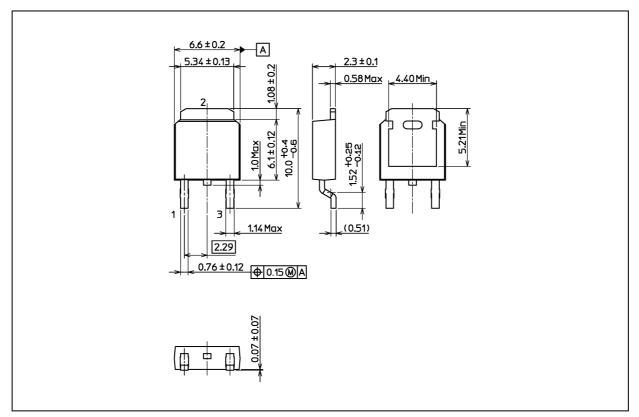
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TK3P80E

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)	
TOSHIBA: 2-7K1S		
Nickname: DPAK		

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